

Takehito Kodzasa

List of Publications by Year in descending order

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62
papers

788
citations

759233

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62
docs citations

62
times ranked

974
citing authors

#	ARTICLE	IF	CITATIONS
1	Atmospheric-pressure plasma oxidation of aluminum for large-area electronics. <i>Journal of Applied Physics</i> , 2019, 125, 215501.	2.5	8
2	Wettability control with self-assembler patterning for printed electronics. <i>Japanese Journal of Applied Physics</i> , 2019, 58, 041002.	1.5	5
3	Thin film transistor performance of amorphous indium-zinc oxide semiconductor thin film prepared by ultraviolet photoassisted sol-gel processing. <i>Japanese Journal of Applied Physics</i> , 2018, 57, 05GD01.	1.5	5
4	Fabrication and performance of pressure-sensing device consisting of electret film and organic semiconductor. <i>Japanese Journal of Applied Physics</i> , 2017, 56, 04CL09.	1.5	3
5	Effect of amide bond in gate dielectric polymers on memory performance of organic field-effect transistors. <i>Japanese Journal of Applied Physics</i> , 2014, 53, 05HB13.	1.5	2
6	Effect of Dielectric Behavior of Gate Dielectric Polymers on Memory Characteristics of Organic Field-effect Transistors. <i>Journal of Photopolymer Science and Technology = [Fotoporima Konwakai Shi]</i> , 2014, 27, 333-337.	0.3	2
7	Effect of Microwave Annealing on Oxide-Semiconductor-Precursor Ink. <i>Journal of Photopolymer Science and Technology = [Fotoporima Konwakai Shi]</i> , 2014, 27, 339-342.	0.3	7
8	Work Function Controlled Zn:Cu Electrode for All-Printed Polymer Diode. <i>Japanese Journal of Applied Physics</i> , 2012, 51, 02BK05.	1.5	0
9	Work Function Controlled Zn:Cu Electrode for All-Printed Polymer Diode. <i>Japanese Journal of Applied Physics</i> , 2012, 51, 02BK05.	1.5	1
10	Printed metal electrode for flexible devices. <i>EPJ Applied Physics</i> , 2011, 55, 23906.	0.7	0
11	Time variation of source-drain current for organic field-effect transistors with dipoles of insulator surface. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2011, 8, 601-603.	0.8	1
12	Short-time-scale threshold voltage shifts in organic field-effect transistors caused by dipoles on insulator surface. <i>Physics Procedia</i> , 2011, 14, 217-220.	1.2	0
13	Printed Electrode for All-Printed Polymer Diode. <i>Japanese Journal of Applied Physics</i> , 2011, 50, 04DK16.	1.5	4
14	Work Function Controlled Printed Metal Alloy Pattern Prepared by Using Pressure Annealing Technique. <i>Materials Research Society Symposia Proceedings</i> , 2011, 1288, 1.	0.1	0
15	Transient Drain Current Measurement for Polymer Transistor Containing Residual Bromine Atoms. <i>Japanese Journal of Applied Physics</i> , 2011, 50, 081604.	1.5	0
16	Transient Drain Current Measurement for Polymer Transistor Containing Residual Bromine Atoms. <i>Japanese Journal of Applied Physics</i> , 2011, 50, 081604.	1.5	0
17	Development of Field-Effect Transistor-Type Photorewritable Memory Using Photochromic Interface Layer. <i>Japanese Journal of Applied Physics</i> , 2010, 49, 04DK09.	1.5	25
18	Mechanical Sintering Techniques for Printed Electrodes with Various Work-function on a Plastic Substrate. <i>Materials Research Society Symposia Proceedings</i> , 2009, 1196, 34.	0.1	0

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19	Development of SiO ₂ Dielectric Thin Film Prepared by the Low-temperature Solution Process. Materials Research Society Symposia Proceedings, 2009, 1196, 46.	0.1	0
20	Device characteristics of back channel-modified organic thin-film transistors. Physica Status Solidi C: Current Topics in Solid State Physics, 2008, 5, 3178-3180.	0.8	0
21	Reduction of threshold voltage fluctuation for organic field effect transistors by increase of insulator capacitance. Thin Solid Films, 2008, 516, 2739-2742.	1.8	5
22	Low Temperature Solution-Based Fabrications of Metal Oxide Semiconductor Films by Mechanical Sintering. Materials Research Society Symposia Proceedings, 2008, 1113, 1.	0.1	0
23	Silicon Oxide Composite Film Fabricated by Wet Process at Low Temperature as a Passivation Layer for Printable Electric Device. Materials Research Society Symposia Proceedings, 2008, 1113, 1.	0.1	0
24	Influence of fine roughness of insulator surface on threshold voltage stability of organic field-effect transistors. Applied Physics Letters, 2008, 93, .	3.3	44
25	Effect of Built-in Potential under Drain Electrodes on Threshold Voltage of Organic Field-Effect Transistors. Japanese Journal of Applied Physics, 2007, 46, L883-L885.	1.5	3
26	Highly Sensitive Organic Photo-FET Using Photosensitive Polymer Insulator. Molecular Crystals and Liquid Crystals, 2007, 471, 21-27.	0.9	2
27	Threshold voltage stability of organic field-effect transistors for various chemical species in the insulator surface. Applied Physics Letters, 2007, 91, .	3.3	66
28	Importance of Semiconductor/Insulator Interface for Improving Transistor Properties of OFET. Molecular Crystals and Liquid Crystals, 2006, 455, 327-332.	0.9	1
29	Interfacial control for developing organic rewritable optical memory using organic photo-FET having photosensitive gate dielectric. , 2006, 6336, 196.		0
30	Improving photo-switching property of organic photo-FET having photosensitive gate dielectric. , 2006, 6336, 204.		0
31	Polymer-Clay Hybrid Dielectric Layer for Flexible Organic Thin Film Transistors. Materials Research Society Symposia Proceedings, 2006, 939, 1.	0.1	0
32	Device Characteristics of p-doped Regioregular Poly(alkylthiophene)-Based Field-Effect Transistors. , 2005, , SSuB4.		0
33	Electrode Effects of Organic Thin-Film Transistor with Top and Bottom Contact Configuration. Japanese Journal of Applied Physics, 2005, 44, 3715-3720.	1.5	13
34	The organic FET with poly(peptide) derivatives and poly(methyl-methacrylate) gate dielectric. Synthetic Metals, 2005, 153, 405-408.	3.9	21
35	Influence of moisture on device characteristics of polythiophene-based field-effect transistors. Journal of Applied Physics, 2004, 95, 5088-5093.	2.5	229
36	Influence of the Atmosphere On the Electric Behavior of A Polymeric Field Effect Transistor. Molecular Crystals and Liquid Crystals, 2004, 424, 209-215.	0.9	0

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37	Subthreshold behavior in nanoparticle-dispersed poly(3-hexylthiophene) FET. , 2004, 5522, 89.		1
38	Device Characteristics of Polythiophene-based Field-effect Transistors Fabricated under Various Conditions. Journal of Photopolymer Science and Technology = [Fotoporima Konwakai Shi], 2004, 17, 327-332.	0.3	2
39	Investigation for surface modification of polymer as an insulator layer of organic FET. Thin Solid Films, 2003, 438-439, 378-381.	1.8	55
40	Surface Potential Control of an Insulator Layer for the High Performance Organic FET. Synthetic Metals, 2003, 137, 967-968.	3.9	89
41	High Performance Organic FET with Double-Semiconductor Layers. Synthetic Metals, 2003, 137, 893-894.	3.9	16
42	Surface plasmon resonance effect on photocurrent amplification. Synthetic Metals, 2003, 137, 1443-1444.	3.9	8
43	Memory effects of pentacene MFS-FET. Synthetic Metals, 2003, 137, 943-944.	3.9	11
44	Optimization of p/n multilayer structure for organic photoreceptor device. Synthetic Metals, 2003, 137, 1481-1482.	3.9	0
45	Low-voltage operation of the organic thin film transistor with a diagonal configuration. , 2003, 5217, 133.		2
46	Gate Bias Modulated Current Flow Analysis at Organic Semiconductor / Metal Interface for Developing High Performance Organic Fet. Materials Research Society Symposia Proceedings, 2002, 734, 9321.	0.1	1
47	High Performance Organic Field Effect Transistor Withanovel Top-And-Bottom Contact (TBC) Structure. Materials Research Society Symposia Proceedings, 2002, 736, 1.	0.1	3
48	Fabrication of a one-dimensional superlattice by alternative deposition of dioxime platinum complexes on KBr (100) surface. Colloids and Surfaces A: Physicochemical and Engineering Aspects, 2002, 198-200, 339-345.	4.7	2
49	Effects of Various Deposition Conditions on the Structure of Platinum Complex Films. Molecular Crystals and Liquid Crystals, 2000, 349, 315-318.	0.3	1
50	Spectroscopic Ellipsometry Study of Thin Film of Gold Iodide with Stearylammonium. Molecular Crystals and Liquid Crystals, 2000, 349, 115-118.	0.3	0
51	Preparation of Thin Film of Layer Structured Bismuth Iodide with a Long Chain Alkylammonium and its Nonlinear Optical Property. Molecular Crystals and Liquid Crystals, 2000, 343, 71-75.	0.3	5
52	Fabrication of a Superstructured One-Dimensional Alloy in a Thin Film Using Bis(dimethylglyoximato)metal(II). Chemistry of Materials, 2000, 12, 940-945.	6.7	5
53	Magnetic, optical, and electrochemical properties of spin transition metal complexes. Synthetic Metals, 1999, 103, 2675-2678.	3.9	2
54	Third order nonlinear optical properties of gold iodide with alongalkyl chain. Synthetic Metals, 1999, 102, 1560-1561.	3.9	5

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55	Synthesis of oriented zeolite film on mercury surface. <i>Studies in Surface Science and Catalysis</i> , 1997, , 2225-2232.	1.5	13
56	Effects of The Substituents on the Nonlinear Optical Properties of Bis(1,2-Diaryl-1,2-Ethylenedithiolato)Metal Complexes. <i>Molecular Crystals and Liquid Crystals</i> , 1996, 286, 275-280.	0.3	12
57	Nonlinear Optical Properties of One-Dimensional Platinum Complexes. <i>Molecular Crystals and Liquid Crystals</i> , 1996, 286, 281-286.	0.3	0
58	Alloying of Linear Metal Chains in the One-Dimensional Metal Complexes and Their THG Property. <i>Molecular Crystals and Liquid Crystals</i> , 1995, 267, 117-122.	0.3	5
59	Dispersed Thin Films of Mixed-Valence One-Dimensional Tetranuclear Platinum Complex and Their Optical Properties. <i>Molecular Crystals and Liquid Crystals</i> , 1995, 267, 123-128.	0.3	2
60	Structure of Physical Gels Formed in Syndiotactic Polystyrene/Solvent Systems Studied by Small-Angle Neutron Scattering. <i>Macromolecules</i> , 1994, 27, 1349-1354.	4.8	47
61	Conformational Ordering Process on Physical Gelation of Syndiotactic Polystyrene/Solvent Systems Revealed by Time-Resolved Infrared Spectroscopy. <i>Applied Spectroscopy</i> , 1993, 47, 1417-1424.	2.2	40
62	Temporal Changes in Sourceâ€œDrain Current for Organic Field-Effect Transistors Caused by Dipole on Insulator Surface. <i>Applied Physics Express</i> , 0, 1, 061801.	2.4	14